

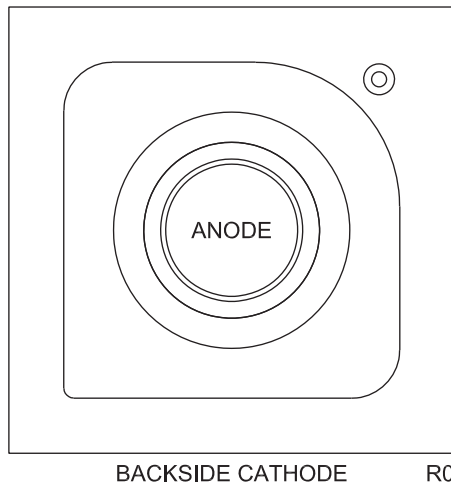
PROCESS CPD102X
Schottky Diode
High Voltage Schottky Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

210,600

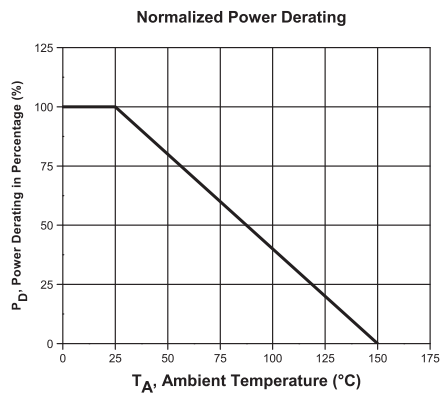
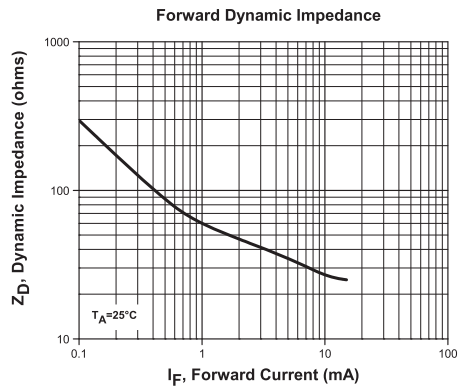
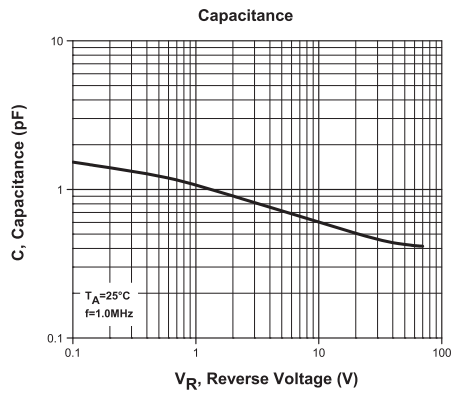
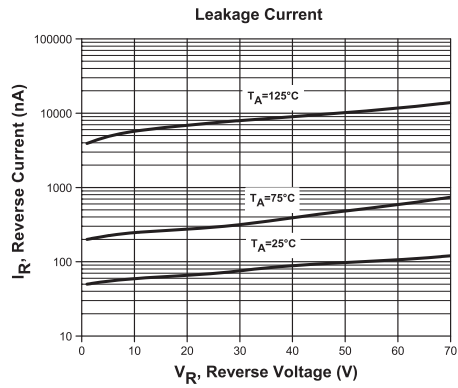
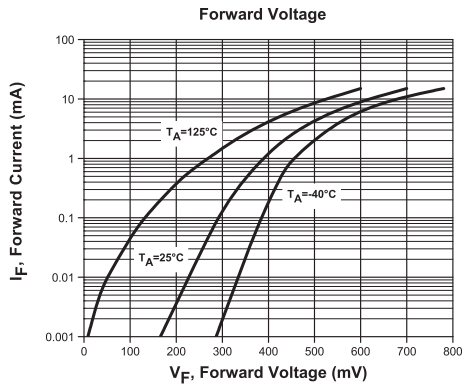
PRINCIPAL DEVICE TYPES

CMDD6263
CMKD6263
CMLD6263 Series
CMOD6263
CMPD6263 Series
CMSD6263 Series
CMUD6263E Series
1N6263

R0 (27-September 2010)

PROCESS CPD102X

Typical Electrical Characteristics



R0 (27-September 2010)